

2SD1250, 2SD1250A

Silicon NPN Triple-Diffused Planar Type

Power Amplifier

TV Vertical Deflection Output

Complementary Pair with 2SB928, 2SB928A

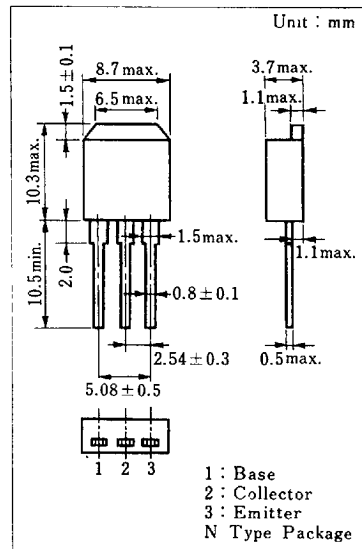
■ Features

- High DC current gain (h_{FE}) and good linearity
- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- "N Type" package configuration with a cooling fin for direct soldering on PC board of a small-size electronic equipment

■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	2SD1250	200	V
	2SD1250A	200	
Collector-emitter voltage	2SD1250	150	V
	2SD1250A	180	
Emitter-base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	3	A
Collector current	I_C	2	A
Collector power dissipation	$T_c = 25^\circ\text{C}$	30	W
	$T_a = 25^\circ\text{C}$	1.3	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

■ Package Dimensions



*Surface-mount type is also available.
(Refer to p.82.)

■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=200\text{ V}, I_E=0$			50	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=4\text{ V}, I_C=0$			50	μA
Collector-base voltage	V_{CBO}	$I_C=500\ \mu\text{A}, I_E=0$	200			V
Collector-emitter voltage	2SD1250	$I_C=5\text{ mA}, I_B=0$	150			V
	2SD1250A		180			
Emitter-base voltage	V_{EBO}	$I_E=500\ \mu\text{A}, I_C=0$	6			V
DC current gain	h_{FE1} *	$V_{CE}=10\text{ V}, I_C=150\text{ mA}$	60		240	
	h_{FE2}	$V_{CE}=10\text{ V}, I_C=400\text{ mA}$	50			
Base-emitter voltage	V_{BE}	$V_{CE}=10\text{ V}, I_C=400\text{ mA}$			1	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{ mA}, I_B=50\text{ mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=0.5\text{ A}, f=1\text{ MHz}$		20		MHz

* h_{FE1} Classifications

Class	Q	P
h_{FE1}	60 ~ 140	100 ~ 240

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